

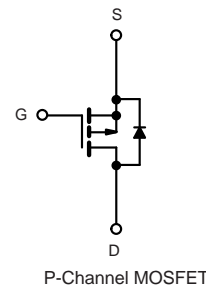
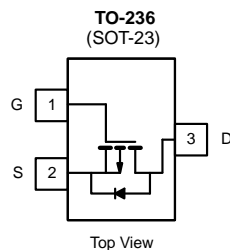
SQ2361AEES-T1_GE3-VB Datasheet

P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) Typ.	I _D (A) ^d	Q _g (TYP.)
-60	0.070 at V _{GS} = -10 V	-4.5	10.1 nC
	0.085 at V _{GS} = -4.5 V	-4.0	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC


RoHS
 COMPLIANT


ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	-4.5
		T _C = 70 °C	-4.0
		T _A = 25 °C	-3.5 ^{a,b}
		T _A = 70 °C	-3.0 ^{a,b}
Pulsed Drain Current (t = 100 μs)	I _{DM}	-20	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	-2.1 ^{a,b}
Avalanche Current	I _{AS}	-15	mJ
Single-Pulse Avalanche Energy	E _{AS}	11.25	
Maximum Power Dissipation	P _D	T _C = 25 °C	4.2
		T _C = 70 °C	2.7
		T _A = 25 °C	2 ^{a,b}
		T _A = 70 °C	1.3 ^{a,b}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^a	R _{thJA}	100	130	°C/W
Maximum junction-to-case (drain)	R _{thJF}	60	75	

Notes

- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 110 °C/W.
- Based on T_C = 25 °C.

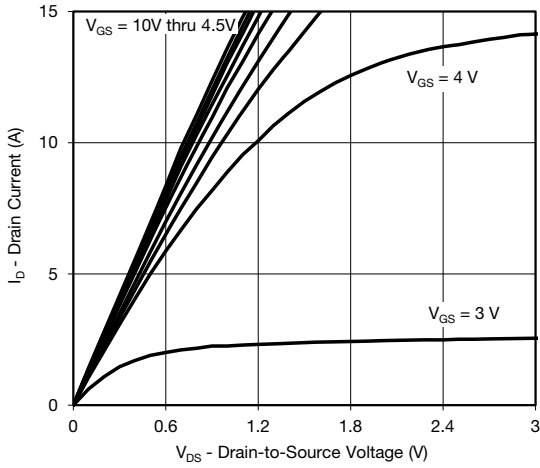
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA	-60	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = -250 μA	-	-6.7	-	mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J		-	4.3	-	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-1	-	-3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -60 V, V _{GS} = 0 V	-	-	-1	μA
		V _{DS} = -60 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ -10 V, V _{GS} = -10 V	-30	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -10 V, I _D = -3.5 A	-	0.070	-	Ω
		V _{GS} = -4.5 V, I _D = -2.8 A	-	0.085	-	
Forward Transconductance ^a	g _{fs}	V _{DS} = -30 V, I _D = -3.5 A	-	11	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = -30 V, V _{GS} = 0 V, f = 1 MHz	-	832	-	pF
Output Capacitance	C _{oss}		-	88	-	
Reverse Transfer Capacitance	C _{rss}		-	63	-	
Total Gate Charge	Q _g	V _{DS} = -30 V, V _{GS} = -10 V, I _D = -3.5 A	-	20	30	nC
		V _{DS} = -30 V, V _{GS} = -4.5 V, I _D = -3.5 A	-	10.1	15.2	
Gate-Source Charge	Q _{gs}		-	3.3	-	
Gate-Drain Charge	Q _{gd}	-	3.9	-		
Gate Resistance	R _g	f = 1 MHz	1.8	9	18	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = -30 V, R _L = 10.7 Ω I _D ≅ -2.8 A, V _{GEN} = -10 V, R _g = 1 Ω	-	8	16	ns
Rise Time	t _r		-	6	12	
Turn-Off Delay Time	t _{d(off)}		-	35	53	
Fall Time	t _f		-	16	24	
Turn-On Delay Time	t _{d(on)}	V _{DD} = -30 V, R _L = 10.7 Ω I _D ≅ -2.8 A, V _{GEN} = -4.5 V, R _g = 1 Ω	-	40	60	
Rise Time	t _r		-	28	42	
Turn-Off Delay Time	t _{d(off)}		-	31	47	
Fall Time	t _f		-	15	23	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	-3.5	A
Pulse Diode Forward Current (t = 100 μs)	I _{SM}		-	-	-20	
Body Diode Voltage	V _{SD}	I _S = -2.8 A, V _{GS} = 0 V	-	-0.85	-1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = -2.8 A, di/dt = 100 A/μs, T _J = 25 °C	-	32	48	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	45	68	nC
Reverse Recovery Fall Time	t _a		-	24	-	ns
Reverse Recovery Rise Time	t _b		-	8	-	

Notes

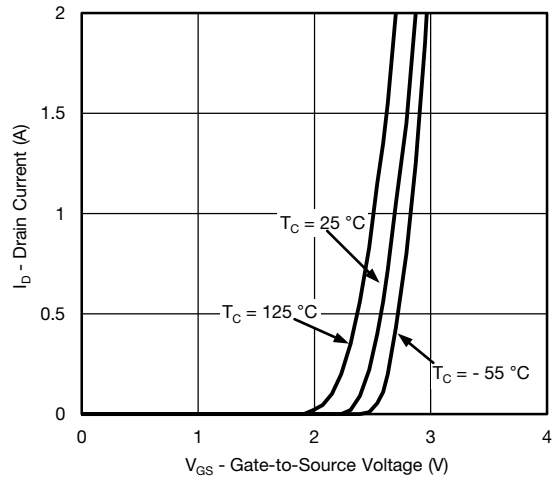
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

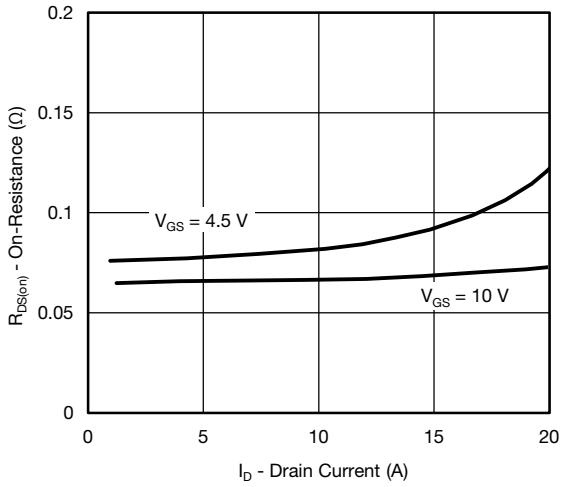
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



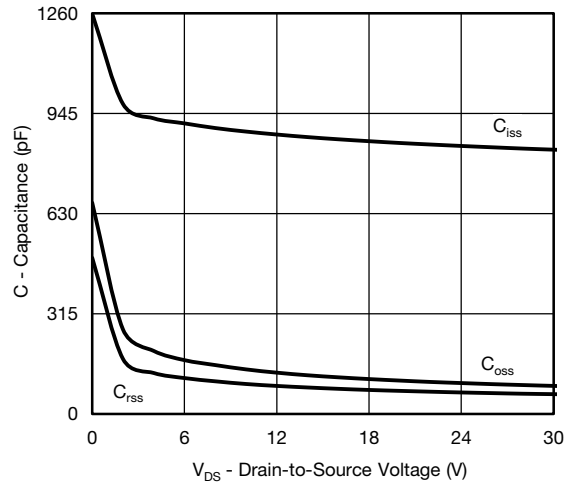
Output Characteristics



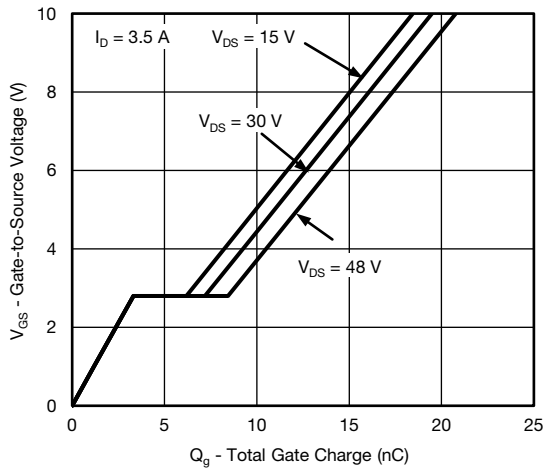
Transfer Characteristics



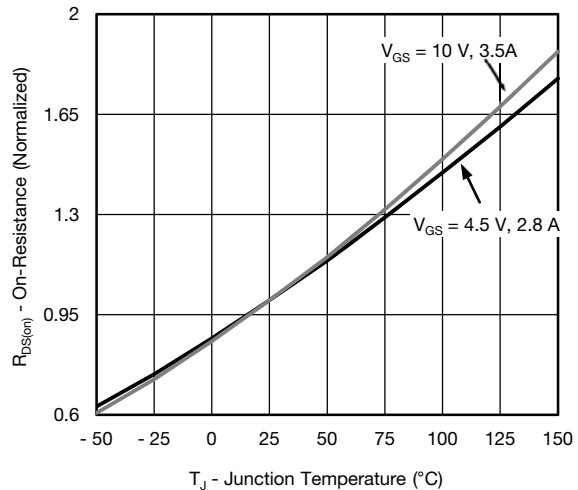
On-Resistance vs. Drain Current



Capacitance

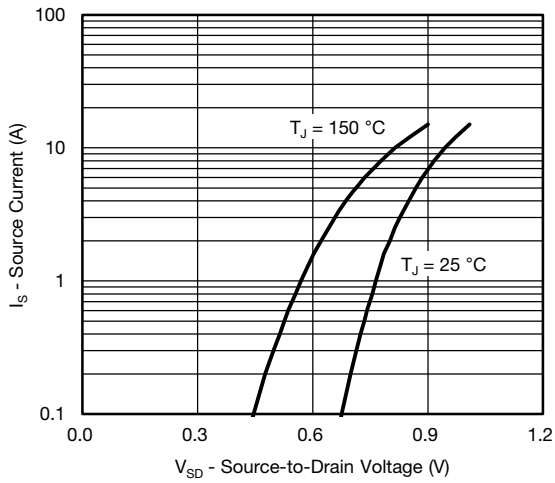


Gate Charge

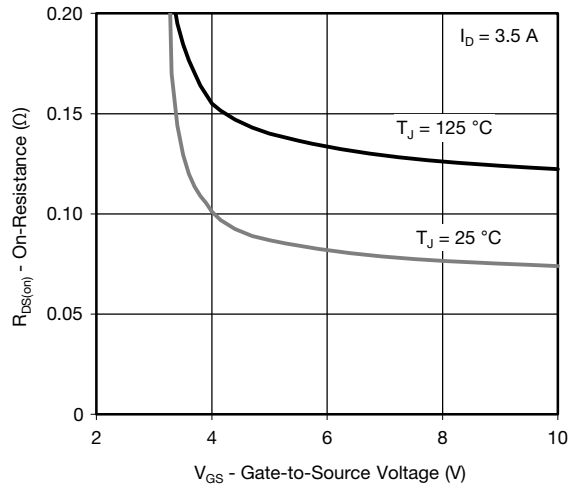


On-Resistance vs. Junction Temperature

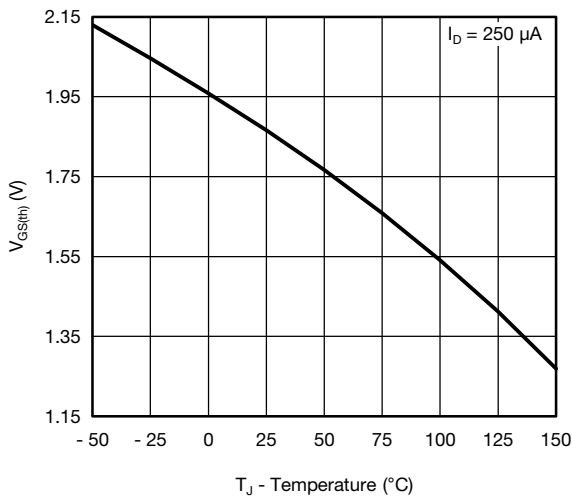
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



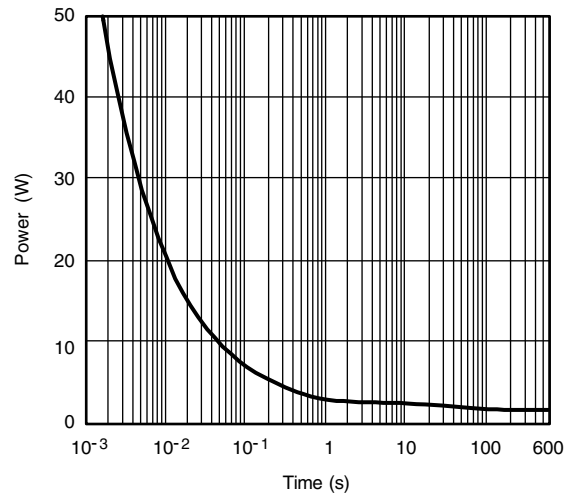
Source-Drain Diode Forward Voltage



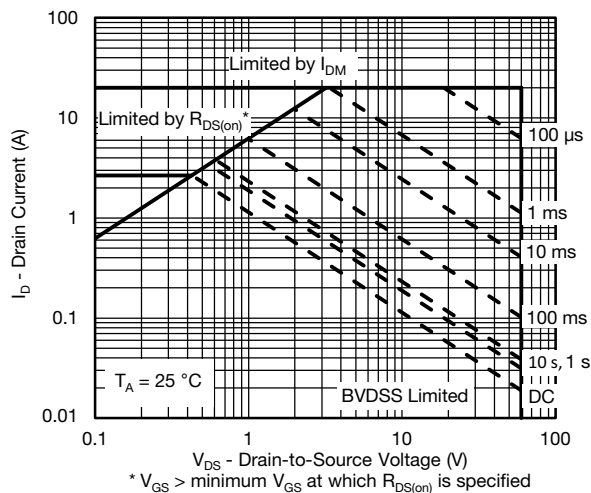
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

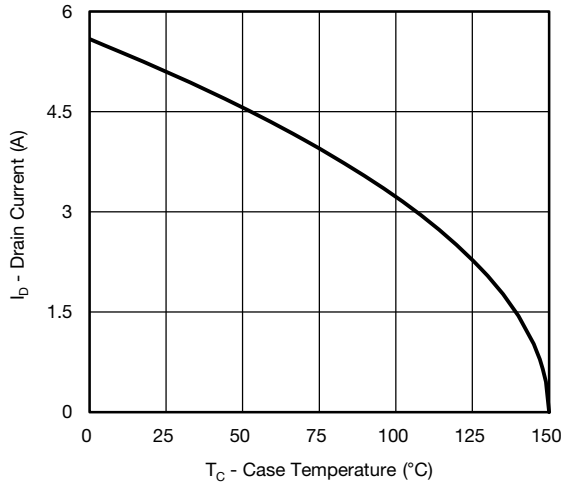


Single Pulse Power, Junction-to-Ambient

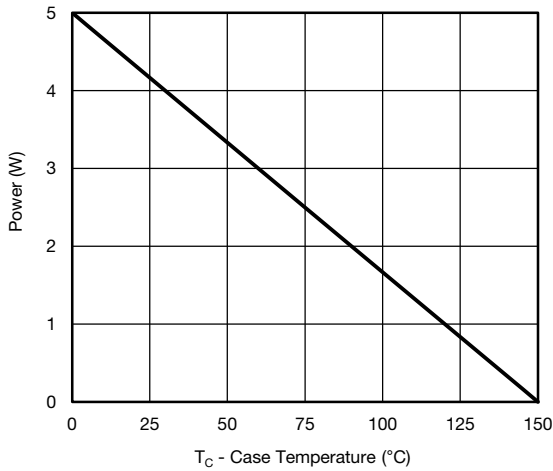


Safe Operating Area

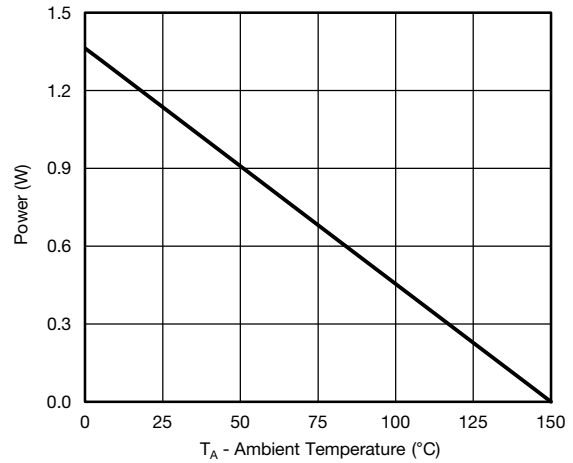
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



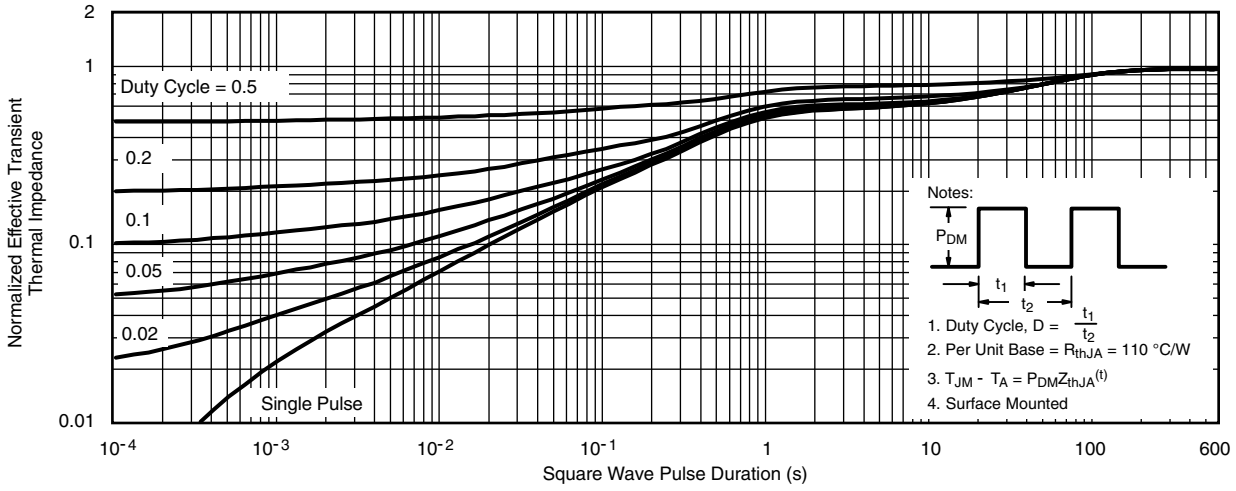
Power, Junction-to-Foot



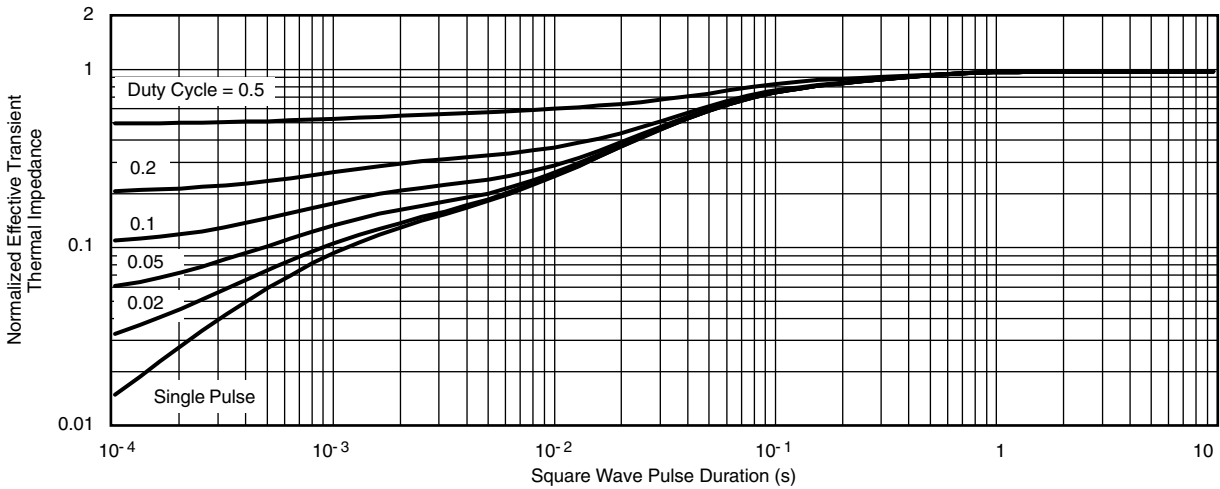
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

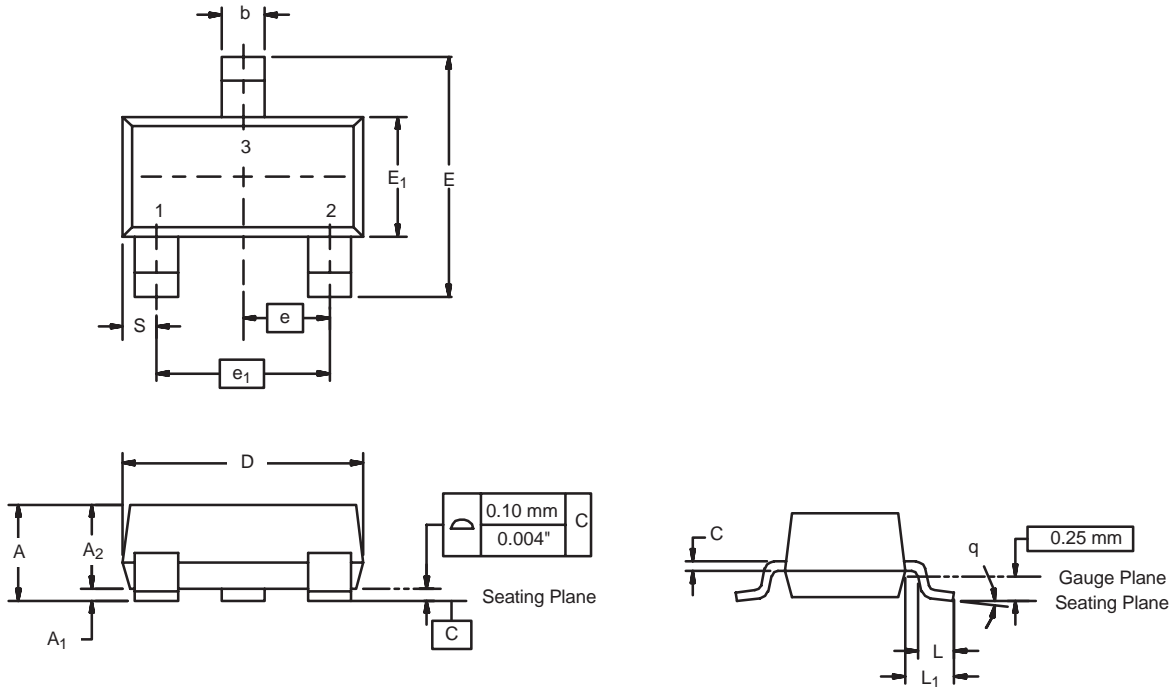


Normalized Thermal Transient Impedance, Junction-to-Ambient



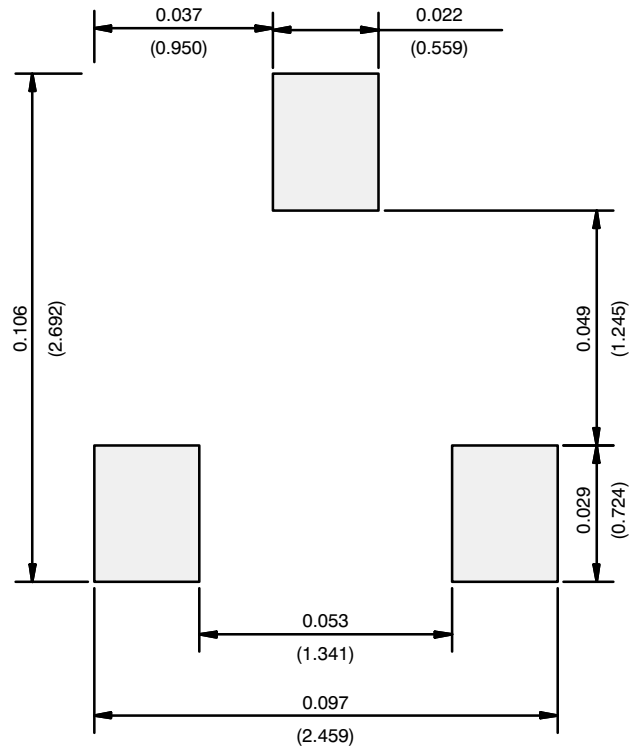
Normalized Thermal Transient Impedance, Junction-to-Foot

SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01				
DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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